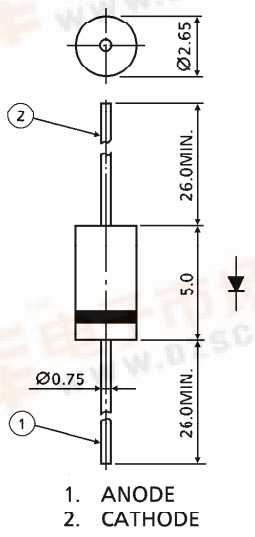
TOSHIBA FAST RECOVERY DIODE SILICON DIFFUSED TYPE

TFR1N, TFR1T

STROBO FLASHER APPLICATIONS. (FAST RECOVERY)

Unit in mm

- Average Forward Current : $I_{F(AV)}$ = 0.5A
- Repetitive Peak Reverse Voltage : V_{RRM} = 1000, 1500V
- Reverse Recovery Time : t_{rr} = 10μs



1. ANODE
2. CATHODE

JEDEC	DO-41
EIAJ	—
TOSHIBA	3-3C1A

Weight : 0.3g

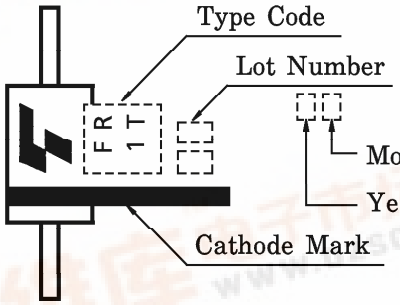
MAXIMUM RATINGS

CHARACTERISTIC		SYMBOL	RATING	UNIT
Repetitive Peak Reverse Voltage	TFR1N	V_{RRM}	1000	V
	TFR1T		1500	
Average Forward Current		$I_{F(AV)}$	0.5	A
I^2t Limit Value (t=1~10ms)		I^2t	2	A^2s
Peak One Cycle Surge Forward Current (Non Repetitive)		I_{FSM}	20	A
Junction Temperature		T_j	−40~125	°C
Storage Temperature Range		T_{stg}	−40~125	°C

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Peak Forward Voltage	V_{FM}	I_{FM} = 0.5A	—	—	1.3	V
Repetitive Peak Reverse Current	I_{RRM}	V_{RRM} = Rated	—	—	10	μA
Reverse Recovery Time	t_{rr}	I_F = 20mA, I_R = 1mA	—	—	10	μs

MARKING



Color : Yellow

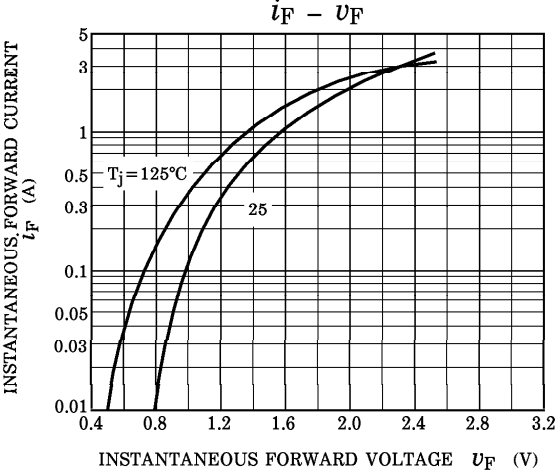
Month (Starting from Alphabet A)

Year (Last Number of the Christian Era)

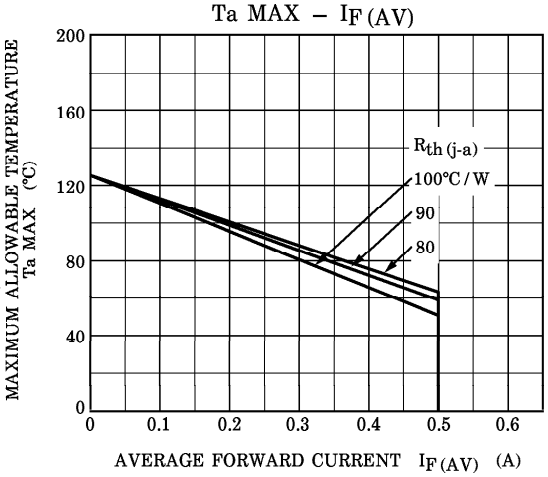
CODE	TYPE
FR1N	TFR1N
FR1T	TFR1T

961001EAA2

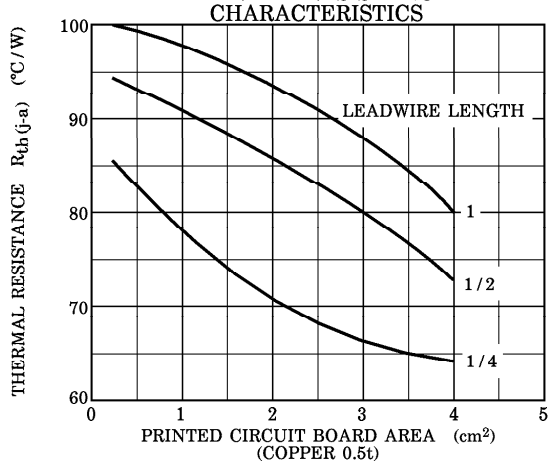
$i_F - v_F$



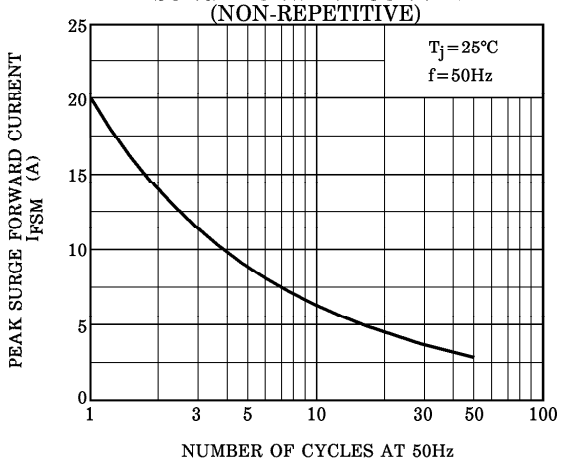
Ta MAX – $I_{F(AV)}$



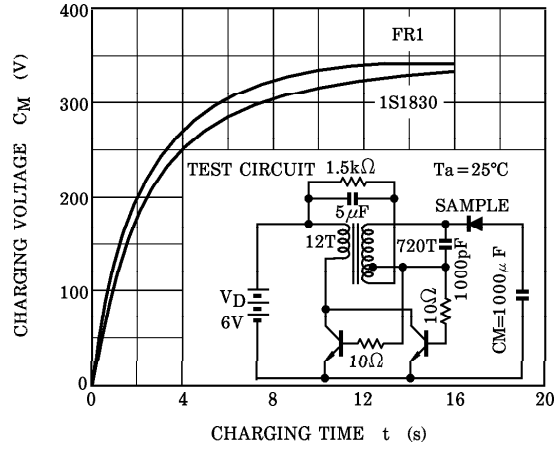
THERMAL RESISTANCE CHARACTERISTICS



SURGE FORWARD CURRENT (NON-REPETITIVE)



C_M CHARGING CHARACTERISTICS



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